

#3 P. Br

11-27-01

500.40681X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : T. Ohyanagi et al.

Serial No.: Not yet assigned

Filed: September 28, 2001

For: FIELD EFFECT TRANSISTOR AND SEMICONDUCTOR  
DEVICE MANUFACTURING METHOD

Group:

Examiner:

jc714 U.S. PTO  
09/9648009  
09/28/01



**INFORMATION DISCLOSURE STATEMENT  
UNDER 37 CFR 1.97 & 1.98**

Assistant Commissioner  
for Patents  
Washington, D.C. 20231

September 28, 2001

Sir:

In the matter of the above-identified application,  
applicants are submitting herewith copies of the documents  
listed in the attached form equivalent to Form PTO-1449 for  
the Examiner's consideration.

This information disclosure statement is being submitted  
with the new application.

Each of the documents listed on the attached form  
equivalent to Form PTO-1449 is in the English language.

It is respectfully requested that this information  
disclosure statement be considered by the Examiner.

Please charge any shortage in the fees due in connection

with the filing of this paper, including extension of time fees, to the deposit account of Antonelli, Terry, Stout & Kraus Deposit Account No. 01-2135 (500.40681X00) please credit any excess fees to such deposit account.

Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP



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<b>Form PTO-1449</b>		<b>U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</b>		<b>ATTY. DKT. NO.</b> 500.40681X00	<b>SERIAL NO.</b> Not yet assigned
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)		<b>APPLICANT</b> T. Ohyanagi et al.			
		<b>FILING DATE</b> Sept. 28, 2001	<b>GROUP</b>		

**U.S. PATENT DOCUMENTS**

<b>Examiner Initial</b>		<b>Document Number</b>	<b>Date</b>	<b>Name</b>		<b>Class</b>	<b>Subclass</b>	<b>Filing Date</b>
	AA							
	AB							
	AC							
	AD							

JC714 U.S. PTO  
09/28/01**FOREIGN PATENT DOCUMENTS**

<b>Examiner Initial</b>		<b>Document Number</b>	<b>Date</b>	<b>Country</b>	<b>Class</b>	<b>Subclass</b>	<b>Translation /Abstract</b>	
							<b>Yes</b>	<b>No</b>
	AM	A-11-121742	4/30/99	Japan			X	
	AN	A-05-129602	5/25/93	Japan			X	
	AO	A-07-086580	3/31/95	Japan			X	
	AP	A-05-110080	4/30/93	Japan			X	

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	AU	IEDM 89, "Asymmetrical Halo Source GOLD drain (HS-GOLD) Deep Sub-half Micron n-MOSFET Design for Reliability and Performance" pp. 617-620
	AV	
	AW	
	AX	
	AY	
	AZ	

<b>Examiner</b>	<b>Date Considered</b>
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